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# RJK4012DPE

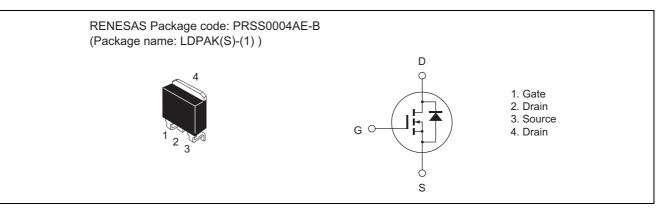
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1575-0100 Rev.1.00 Aug 08, 2007

# Features

- Low on-resistance
- Low leakage current
- High speed switching

## Outline



# **Absolute Maximum Ratings**

|   |                                  |             | $(Ta = 25^{\circ}C)$ |
|---|----------------------------------|-------------|----------------------|
| Item  | Symbol                           | Ratings     | Unit                 |
| Drain to source voltage                     | V <sub>DSS</sub>                 | 400         | V                    |
| Gate to source voltage                      | V <sub>GSS</sub>                 | ±30         | V                    |
| Drain current                               | I <sub>D</sub>                   | 15          | А                    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1     | 45          | А                    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>                  | 15          | А                    |
| Body-drain diode reverse drain peak current | I <sub>DR (pulse)</sub> Note1    | 45          | А                    |
| Avalanche current                           | I <sub>AP</sub> <sup>Note3</sup> | 5           | А                    |
| Avalanche energy                            | E <sub>AR</sub> <sup>Note3</sup> | 1.4         | mJ                   |
| Channel dissipation                         | Pch Note2                        | 100         | W                    |
| Channel to case thermal impedance           | θch-c                            | 1.25        | °C/W                 |
| Channel temperature                         | Tch                              | 150         | °C                   |
| Storage temperature                         | Tstg                             | -55 to +150 | °C                   |

Notes: 1. PW  $\leq$  10  $\mu s,$  duty cycle  $\leq$  1%

2. Value at Tc =  $25^{\circ}C$ 

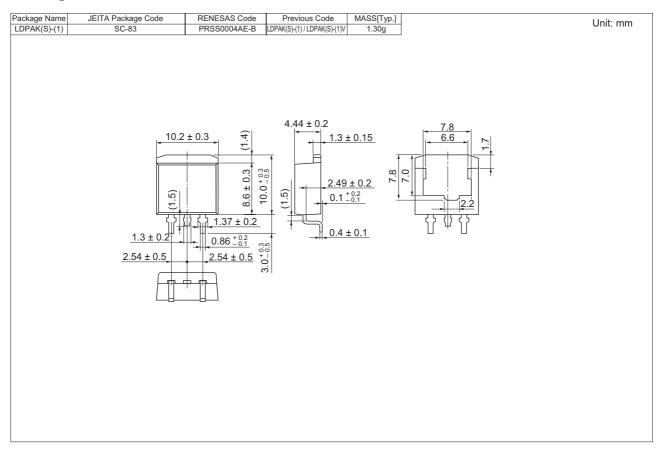
3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

# **Electrical Characteristics**

|  |                      |     |      |      |      | $(Ta = 25^{\circ}C)$   |
|--|----------------------|-----|------|------|------|--|
| ltem                                       | Symbol               | Min | Тур  | Max  | Unit | Test conditions  |
| Drain to source breakdown voltage          | V <sub>(BR)DSS</sub> | 400 | —    | —    | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$                                  |
| Zero gate voltage drain current            | I <sub>DSS</sub>     | _   | —    | 1    | μΑ   | $V_{DS} = 400 \text{ V}, \text{ V}_{GS} = 0$                       |
| Gate to source leak current                | I <sub>GSS</sub>     |     | —    | ±0.1 | μΑ   | $V_{GS} = \pm 30$ V, $V_{DS} = 0$                                  |
| Gate to source cutoff voltage              | V <sub>GS(off)</sub> | 3.0 | —    | 4.5  | V    | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$              |
| Static drain to source on state resistance | $R_{\text{DS(on)}}$  |     | 0.34 | 0.41 | Ω    | $I_D = 7.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$        |
| Input capacitance                          | Ciss                 | _   | 1100 | _    | pF   | V <sub>DS</sub> = 25 V   |
| Output capacitance                         | Coss                 | _   | 135  | —    | pF   | V <sub>GS</sub> = 0<br>f = 1 MHz                                   |
| Reverse transfer capacitance               | Crss                 | _   | 17   | —    | pF   |  |
| Turn-on delay time                         | t <sub>d(on)</sub>   | _   | 30   | —    | ns   | I <sub>D</sub> = 7.5 A   |
| Rise time                                  | tr                   | _   | 29   | _    | ns   | $V_{GS} = 10 V$<br>$R_L = 26.7 \Omega$<br>$Rg = 10 \Omega$         |
| Turn-off delay time                        | t <sub>d(off)</sub>  |     | 77   | —    | ns   |  |
| Fall time                                  | t <sub>f</sub>       | _   | 19   | _    | ns   |  |
| Total gate charge                          | Qg                   | —   | 29   | —    | nC   | V <sub>DD</sub> = 320 V  |
| Gate to source charge                      | Qgs                  | _   | 5.5  | —    | nC   | V <sub>GS</sub> = 10 V<br>I <sub>D</sub> = 15 A                    |
| Gate to drain charge                       | Qgd                  | _   | 13   | _    | nC   |  |
| Body-drain diode forward voltage           | V <sub>DF</sub>      | _   | 0.91 | 1.55 | V    | $I_F = 15 \text{ A}, V_{GS} = 0^{Note4}$                           |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>      | _   | 260  | _    | ns   | $I_F = 15 \text{ A}, V_{GS} = 0$<br>di <sub>F</sub> /dt = 100 A/µs |

Notes: 4. Pulse test

# **Package Dimensions**



# **Ordering Information**

| Part No.         | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK4012DPE-00-J3 | 1000 pcs | Taping             |

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